

2N5830



NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display driving. Sourced from Process 16. See 2N5551 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	100	V	
V _{CBO}	Collector-Base Voltage	120	V	
V_{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

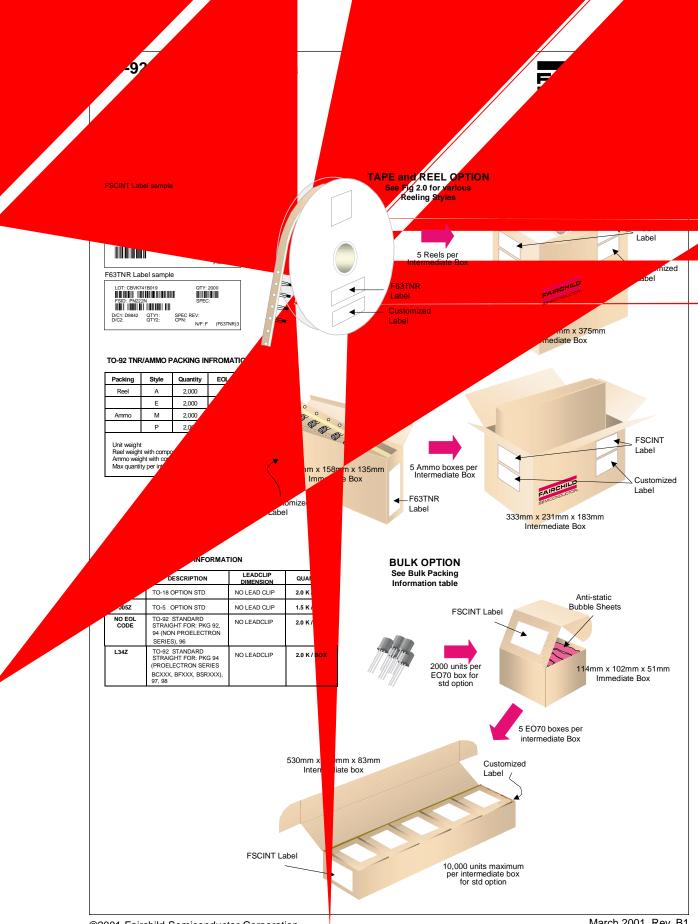
TA = 25°C unless otherwise noted

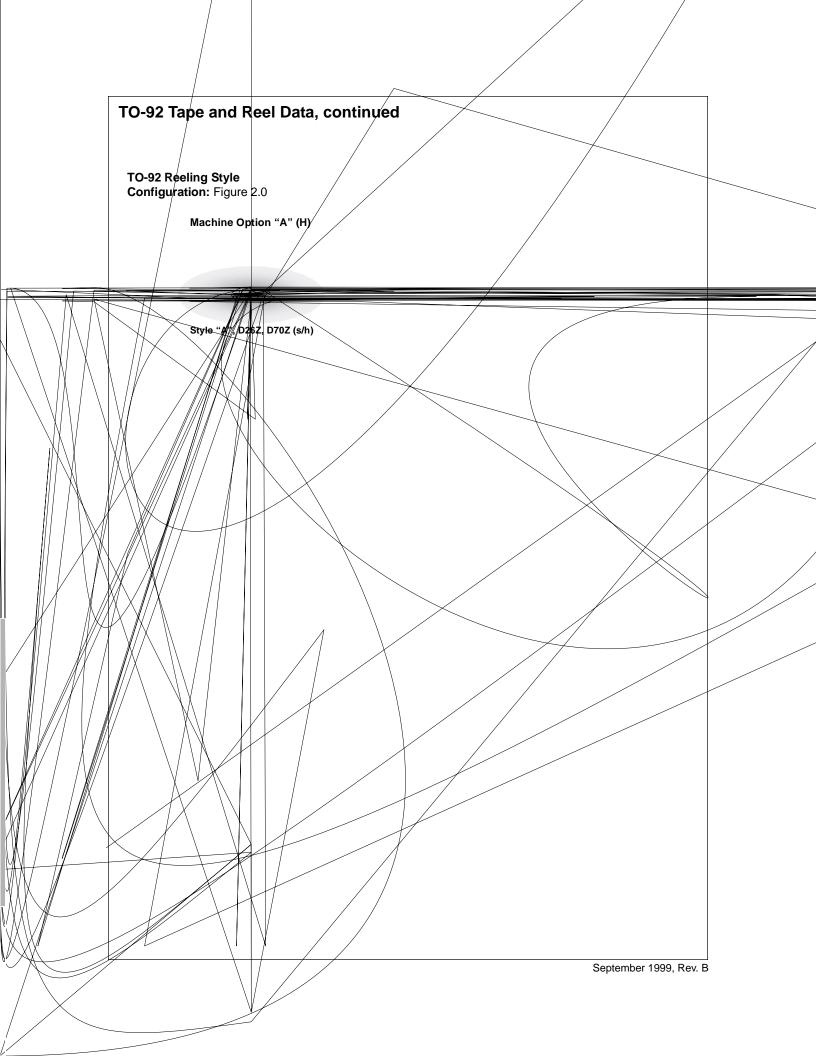
Symbol	Characteristic	Max	Units
		2N5830	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

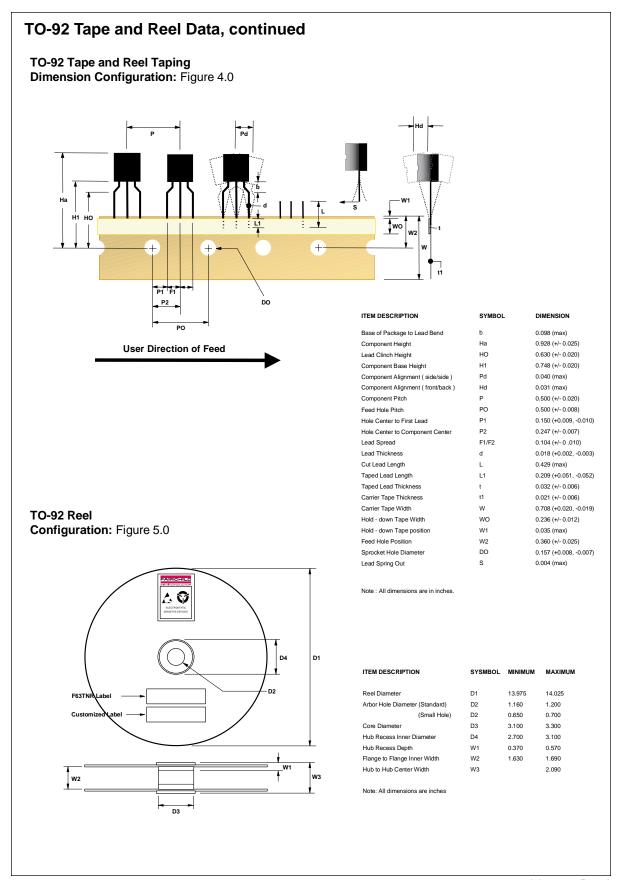
NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	120		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_{E} = 0$		50	nA
		$V_{CB} = 100 \text{ V}, I_{E} = 0, T_{A} = 100 ^{\circ}\text{C}$		25	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		50	nA
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	60		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	80	500	
.,	Calle step Fasitten Ceturation Valtage	$V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$	80	0.45	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.15 0.2	V V
		$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$		8.0	V
		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		1.0	V
\/	Base-Emitter On Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$		1.0 0.8	V
V _{BE(on)}	Base-Emilier On Vollage	V CE = 3.0 V, IC = 1.0 IIIA		0.0	V
SMALL S	IGNAL CHARACTERISTICS				
C _{cb}	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		4.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	1.0	5.0	
h _{ie}	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$		6.0	ΚΩ
h _{oe}	Output Admittance	f = 1.0 kHz		40	μmho
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^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%



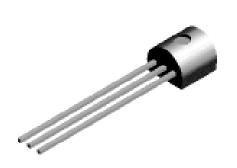


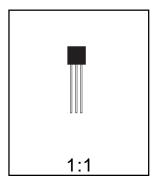


TO-92 Package Dimensions



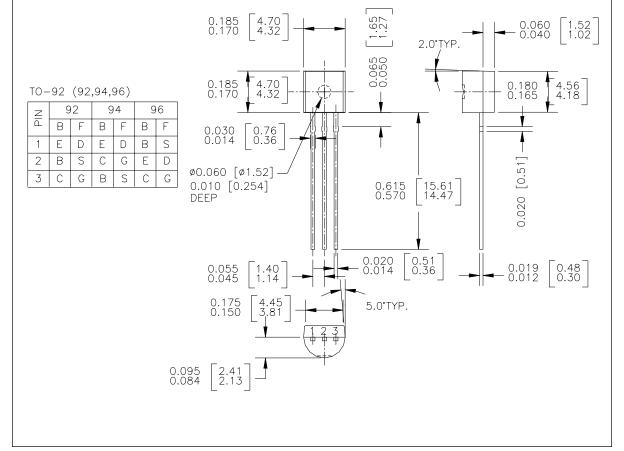
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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